ABSTRACT OF THE DISCLOSURE

In a nonvolatile semiconductor storage device which is electrically writable and erasable, a silicon substrate, a plurality of element isolation portions which project from the silicon substrate and are disposed at a predetermined interval, floating electrodes disposed between the isolation portions, and a control electrode laminated on the isolation portions and the floating electrodes are provided, and an interval between the adjacent floating electrodes is formed greater at the side away from the silicon substrate than at the silicon substrate side.